

Vijay Dixit

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/2736543/publications.pdf>

Version: 2024-02-01

79
papers

822
citations

516710

16
h-index

610901

24
g-index

80
all docs

80
docs citations

80
times ranked

886
citing authors

#	ARTICLE	IF	CITATIONS
1	Transparent p-AgCoO ₂ /n-ZnO diode heterojunction fabricated by pulsed laser deposition. Thin Solid Films, 2007, 515, 7352-7356.	1.8	62
2	Effect of two-step growth process on structural, optical and electrical properties of MOVPE-grown GaP/Si. Journal of Crystal Growth, 2008, 310, 3428-3435.	1.5	38
3	Structural and Electronic Properties of a Mn Oxide Diffusion Barrier Layer Formed by Chemical Vapor Deposition. IEEE Transactions on Device and Materials Reliability, 2011, 11, 295-302.	2.0	38
4	A versatile phenomenological model for the S-shaped temperature dependence of photoluminescence energy for an accurate determination of the exciton localization energy in bulk and quantum well structures. Journal Physics D: Applied Physics, 2014, 47, 065103.	2.8	37
5	Crystal growth and characterization of a new nonlinear optical material: Urea l-Malic Acid. Journal of Crystal Growth, 2003, 253, 460-466.	1.5	35
6	Growth of InSb epitaxial layers on GaAs (001) substrates by LPE and their characterizations. Journal of Crystal Growth, 2002, 235, 154-160.	1.5	26
7	Studies on MOVPE growth of GaP epitaxial layer on Si(001) substrate and effects of annealing. Journal of Crystal Growth, 2006, 293, 5-13.	1.5	25
8	Effect of carrier confinement on effective mass of excitons and estimation of ultralow disorder in Al _x Ga _{1-x} As/GaAs quantum wells by magneto-photoluminescence. Scientific Reports, 2017, 7, 4905.	3.3	24
9	Studies on high resolution x-ray diffraction, optical and transport properties of InAs _x Sb _{1-x} GaAs (x ≈ 1/20.06) heterostructure grown using liquid phase epitaxy. Journal of Applied Physics, 2004, 96, 4989-4997.	2.5	23
10	Observation of electron confinement in InP/GaAs type-II ultrathin quantum wells. Applied Physics Letters, 2010, 97, .	3.3	22
11	Effect of ⁶⁰ Co γ -ray irradiation on electrical properties of GaAs epilayer and GaAs p-n diode. Nuclear Instruments & Methods in Physics Research B, 2011, 269, 272-276.	1.4	22
12	Dislocation-assisted tunnelling of charge carriers across the Schottky barrier on the hydride vapour phase epitaxy grown GaN. Journal of Applied Physics, 2015, 118, .	2.5	21
13	Alloying induced degradation of the absorption edge of InAs _x Sb _{1-x} . Applied Physics Letters, 2007, 90, 101905.	3.3	20
14	High-mobility InSb epitaxial films grown on a GaAs (001) substrate using liquid-phase epitaxy. Applied Physics Letters, 2002, 80, 2102-2104.	3.3	18
15	Effect of high dose γ -ray irradiation on GaAs p-i-n photodetectors. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2015, 785, 93-98.	1.6	17
16	Temperature dependence of the energy gap and free carrier absorption in bulk InAs _{0.05} Sb _{0.95} single crystals. Applied Physics Letters, 2003, 82, 4720-4722.	3.3	16
17	Effect of γ -ray irradiation on breakdown voltage, ideality factor, dark current and series resistance of GaAs p-n diode. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2012, 685, 41-45.	1.6	16
18	Investigation of crystalline and electronic band alignment properties of GaP/Ge(111) heterostructure. Applied Physics Letters, 2014, 104, .	3.3	16

#	ARTICLE	IF	CITATIONS
19	Growth and surface topography of WSe ₂ single crystal. AIP Conference Proceedings, 2016, , .	0.4	16
20	Role of surface energy on the morphology and optical properties of GaP micro & nano structures grown on polar and non-polar substrates. Applied Surface Science, 2017, 419, 957-967.	6.1	16
21	Structural, optical, and electrical properties of bulk single crystals of InAs _x Sb(1- ^x) grown by rotatory Bridgman method. Applied Physics Letters, 2002, 81, 1630-1632.	3.3	15
22	Growth of InBi _x Sb(1- ^x) films on GaAs(001) substrates using liquid phase epitaxy and their characterization. Journal of Crystal Growth, 2002, 241, 171-176.	1.5	15
23	Raman spectroscopy and atomic force microscopy study of interfacial polytypism in GaP/Ge(111) heterostructures. Applied Surface Science, 2018, 427, 754-762.	6.1	15
24	Effect of excess plasma on photoelectron spectra of nanoporous GaP. Applied Physics Letters, 2006, 88, 083115.	3.3	13
25	Surface and interface properties of ZrO ₂ /GaAs, SiO ₂ /GaAs and GaP/GaAs hetero structures investigated by surface photovoltage spectroscopy. Applied Surface Science, 2019, 476, 615-622.	6.1	13
26	Growth of InSb(1- ^x)Bi _x crystals by rotatory Bridgman method and their characterization. Journal of Crystal Growth, 2000, 217, 40-46.	1.5	12
27	Temperature dependence of the photo-induced inverse spin Hall effect in Au/InP hybrid structures. Applied Physics Letters, 2014, 104, 042102.	3.3	11
28	Effect of lithium ion irradiation on the transport and optical properties of Bridgman grown-type InSb single crystals. Journal of Applied Physics, 2001, 90, 1750-1753.	2.5	10
29	A comparative study on nanotextured high density Mg-doped and undoped GaN. Journal of Applied Physics, 2007, 101, 044311.	2.5	10
30	Ultraviolet photoelectron spectroscopy of nano In clusters Schottky barriers on sputtered InP. Applied Surface Science, 2011, 258, 143-146.	6.1	10
31	Determination of band offsets in strained InAs _x P _{1-^x} /InP quantum well by capacitance voltage profile and photoluminescence spectroscopy. Journal of Applied Physics, 2011, 109, .	2.5	10
32	Numerical simulation of inverse spin Hall spectra in Pt/GaAs hybrid structure. Journal Physics D: Applied Physics, 2011, 44, 265104.	2.8	10
33	Charge carrier localization effects on the quantum efficiency and operating temperature range of InAs _x P _{1-^x} /InP quantum well detectors. Journal of Applied Physics, 2016, 119, .	2.5	10
34	Experimental setup for rapid crystallization using favoured chemical potential and hydrodynamic conditions. Bulletin of Materials Science, 2001, 24, 455-459.	1.7	9
35	Structural and compositional analysis of InBi _x As _y Sb(1- ^x - ^y) films grown on GaAs(0 0 1) substrates by liquid phase epitaxy. Applied Surface Science, 2003, 220, 321-326.	6.1	9
36	Temperature dependence of the photoluminescence from InP/GaAs type-II ultrathin quantum wells. Journal Physics D: Applied Physics, 2010, 43, 455410.	2.8	9

#	ARTICLE	IF	CITATIONS
37	Dislocations limited electronic transport in hydride vapour phase epitaxy grown GaN templates: A word of caution for the epitaxial growers. Applied Physics Letters, 2015, 106, .	3.3	9
38	Crystalline and band alignment properties of InAs/Ge (111) heterostructure. Journal of Alloys and Compounds, 2015, 646, 393-398.	5.5	9
39	Electrical and optical characterization of photooxidized TPD. Journal of Materials Chemistry, 2007, 17, 343-348.	6.7	8
40	Conduction band offset and quantum states probed by capacitance-voltage measurements for InP/GaAs type-II ultrathin quantum wells. Journal of Applied Physics, 2011, 109, .	2.5	7
41	Evaluation of structural and microscopic properties of tetragonal ZrO_2 for the facet coating of 980-nm semiconductor laser diodes. Journal Physics D: Applied Physics, 2015, 48, 105102.	2.8	7
42	Effect of disorders on the optical properties of excitons in InAsP/InP quantum wells investigated by magneto-photoluminescence spectroscopy. Journal of the Optical Society of America B: Optical Physics, 2018, 35, 2405.	2.1	7
43	Evaluation of electronic transport properties and conduction band offsets of asymmetric InAs/InGaAs dot-in-well structures. Journal Physics D: Applied Physics, 2012, 45, 365104.	2.8	6
44	Band alignment and quantum states of InAs P δ /InP surface quantum wells investigated from ultraviolet photoelectron spectroscopy and photoluminescence. Materials Letters, 2012, 87, 69-72.	2.6	6
45	Low- and high-density InAs nanowires on Si(100) and their Raman imaging. Semiconductor Science and Technology, 2013, 28, 015025.	2.0	6
46	Observation of anisotropic distribution of microstructure in GaP/GaAs epitaxial layers. Journal of Applied Physics, 2016, 120, .	2.5	6
47	Effect of surface morphology on the optical properties of InAs/Ge (1 1 1). Applied Surface Science, 2016, 372, 70-78.	6.1	6
48	The effect of magnetic field on free and bound exciton luminescence in GaAs/AlGaAs multiple quantum well structures: a quantitative study on the estimation of ultra-low disorder. Journal Physics D: Applied Physics, 2017, 50, 335107.	2.8	6
49	Radiative and non-radiative recombination of thermally activated magneto-excitons probed via quasi-simultaneous photoluminescence and surface-photovoltage spectroscopy. Journal of Applied Physics, 2018, 124, .	2.5	5
50	Development of a simple cost-effective maskless-photolithography system. AIP Conference Proceedings, 2019, , .	0.4	5
51	Transport, optical and magnetotransport properties of hetero-epitaxial InAs $_x$ Sb $_{1-x}$ /GaAs($x \approx 0.06$) and bulk crystals: experiment and theoretical analysis. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 20, 272-277.	2.7	4
52	Optimization of the properties of MOVPE-grown GaP epitaxial layers on GaP (100)B substrates. Semiconductor Science and Technology, 2008, 23, 075031.	2.0	4
53	Micro Raman and Photoluminescence Spectroscopy of Nano-Porous n and p Type GaN/Sapphire(0001). Journal of Nanoscience and Nanotechnology, 2007, 7, 2186-2191.	0.9	3
54	Study of the microstructure information of GaAs epilayers grown on silicon substrate using synchrotron radiation. Journal of Synchrotron Radiation, 2016, 23, 238-243.	2.4	3

#	ARTICLE	IF	CITATIONS
55	Anisotropic distribution of dislocations density in tensile strained GaP/GaAs epilayers. Vacuum, 2018, 154, 214-217.	3.5	3
56	A parallel magnetic field driven confinement versus separation of charges in GaAs quantum well investigated by magneto-photovoltage and magneto-photoluminescence spectroscopy. Journal of Luminescence, 2019, 206, 342-347.	3.1	3
57	Photovoltaic Response and Charge Redistribution Processes in GaAs/AlGaAs Multiple Quantum Wells Structure. Physica Status Solidi (B): Basic Research, 2020, 257, 2000331.	1.5	3
58	Studies of Valence Band Alignment Between Nitrided GaPN/GaP (111) Interface Using X-ray Photoelectron Spectroscopy. AIP Conference Proceedings, 2011, , .	0.4	2
59	Intersubband plasmon-phonon coupling in GaAsP/AlGaAs near surface quantum well. Applied Physics Letters, 2013, 102, 181120.	3.3	2
60	Raman spectroscopy investigation of inter-diffusion in GaP/Ge(111) heterostructures. Superlattices and Microstructures, 2019, 125, 190-197.	3.1	2
61	An Accurate Measurement of Carrier Concentration in an Inhomogeneous GaN Epitaxial Layer from Hall Measurements. Environmental Science and Engineering, 2014, , 767-769.	0.2	2
62	Studies on GaAs/AlGaAs based (p and n-type) quantum well infrared photodetector structures grown using MOVPE. , 2007, , .		1
63	DVCC based voltage-mode multifunctional biquadratic filter. , 2009, , .		1
64	Observation of room temperature optical absorption in InP/GaAs type-II ultrathin quantum wells and quantum dots. Journal of Applied Physics, 2014, 115, 223505.	2.5	1
65	Self-catalyst assisted and catalyst-free epitaxial growth of InAs on Ge (111): Role of substrate surface and evolution of polytypism. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, .	2.1	1
66	Anisotropic distribution of microstructure in compressively strained InP/GaAs epitaxial layers. Superlattices and Microstructures, 2018, 122, 636-642.	3.1	1
67	Investigation of relative content of zinc-blende and wurtzite phases in GaP/Ge(111) using Raman spectroscopy. AIP Conference Proceedings, 2019, , .	0.4	1
68	Simultaneous magneto-electro-optical measurements in modulation-doped quantum well: An investigation on magneto-photoluminescence intensity oscillations. Journal of Applied Physics, 2019, 125, 205701.	2.5	1
69	Electric and magnetic field effects on the exciton localization in a modulation doped InGaAs/GaAs quantum well. AIP Conference Proceedings, 2020, , .	0.4	1
70	Influence of interface states on built-in electric field and diamagnetic-Landau energy shifts in asymmetric modulation-doped InGaAs/GaAs QWs. Journal Physics D: Applied Physics, 2022, 55, 385101.	2.8	1
71	Comparative studies on As-grown and nanotextured GaN:Mg epilayer. , 2007, , .		0
72	Structural, Optical And Electrical Properties Of MOVPE Grown InP/GaAs Type-II Ultrathin Quantum Well. , 2010, , .		0

#	ARTICLE	IF	CITATIONS
73	Quantum States Probed By Temperature Dependence Capacitance-Voltage Measurements For InP ^δ -GaAs Type-II Ultrathin Quantum Well. , 2011, , .		0
74	A comparison of inverse spin hall spectra in Pt/III-V hybrid structures. , 2012, , .		0
75	Development and application of InAsP/InP quantum well infrared detector. AIP Conference Proceedings, 2016, , .	0.4	0
76	Estimation of electron spin polarization from circularly polarized photoluminescence in strained quantum wells. Journal of Applied Physics, 2017, 122, 025703.	2.5	0
77	Role of surface and interface states on the performance of GaAs based photodetectors. AIP Conference Proceedings, 2019, , .	0.4	0
78	Anisotropic magnetic properties of excitons in GaAs multiple quantum wells. Superlattices and Microstructures, 2020, 137, 106332.	3.1	0
79	Effect of germanium auto-diffusion on the bond lengths of Ga and P atoms in GaP/Ge(111) investigated by using X-ray absorption spectroscopy. Journal of Synchrotron Radiation, 2021, 28, 480-489.	2.4	0